

isc Silicon NPN Power Transistor

2SC2650

DESCRIPTION

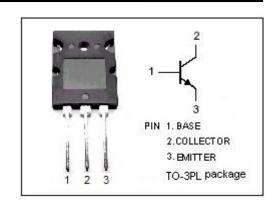
- · Collector-Emitter Breakdown Voltage-
- : V_{(BR)CEO}= 400V(Min)
- · High Switching Speed
- · Wide Area of Safe Operation
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

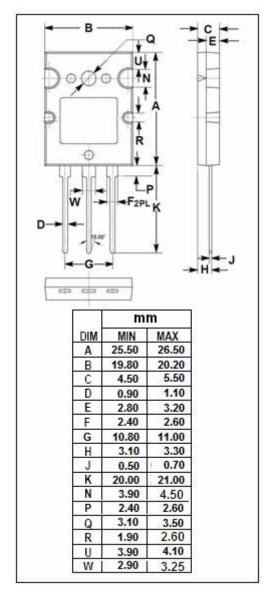
APPLICATIONS

- · Switching regulator application.
- High voltage switching application.
- · High speed DC-DC converter application.

ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

| SYMBOL | PARAMETER | VALUE | UNIT |
|------------------|---|---------|--|
| V _{СВО} | Collector-Base Voltage | 500 | V |
| Vceo | Collector-Emitter Voltage | 400 | V |
| V_{EBO} | Emitter-Base Voltage | 7 | V |
| lc | Collector Current-Continuous | 10 | Α |
| I _B | Base Current-Continuous | 5 | Α |
| Pc | Collector Power Dissipation @ T _C =25℃ | 100 | W |
| TJ | Junction Temperature | 150 | $^{\circ}\!$ |
| T _{stg} | Storage Temperature Range | -55~150 | $^{\circ}$ C |







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ELECTRICAL CHARACTERISTICS

T_c=25℃ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP. | MAX | UNIT | | | |
|----------------------|--------------------------------------|--|-----|------|-----|------------|--|--|--|
| V _{(BR)CBO} | Collector-Base Breakdown Voltage | I _C = 1mA; I _E = 0 | 500 | | | V | | | |
| V _{(BR)CEO} | Collector-Emitter Breakdown Voltage | I _C = 10mA; I _B = 0 | 400 | | | V | | | |
| V _{(BR)EBO} | Emitter-Base Breakdown Voltage | I _E = 1mA; I _C = 0 | 7 | | | V | | | |
| V _{CE(sat)} | Collector-Emitter Saturation Voltage | I _C = 5A; I _B = 0.5A | | | 1.5 | V | | | |
| V _{BE(sat)} | Base-Emitter Saturation Voltage | I _C = 5A; I _B = 0.5A | | | 2.0 | V | | | |
| I _{CBO} | Collector Cutoff Current | V _{CB} = 400V ; I _E = 0 | | | 100 | μА | | | |
| I _{EBO} | Emitter Cutoff Current | V _{EB} = 7V ; I _C = 0 | | | 1 | mA | | | |
| h _{FE} | DC Current Gain | Ic= 5A; Vc== 5V | 10 | | | | | | |
| Switching Times | | | | | | | | | |
| tr | Rise Time | | | | 1.0 | μ S | | | |
| t _{stg} | Storage Time | I _C = 5A; I _{B1} = -I _{B2} = 0.5A; R _L = 40 Ω; V _{CC} = 200V; Duty Cycle≤1% | | | 2.5 | μ \$ | | | |
| t _f | Fall Time | | | | 1.0 | μS | | | |

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